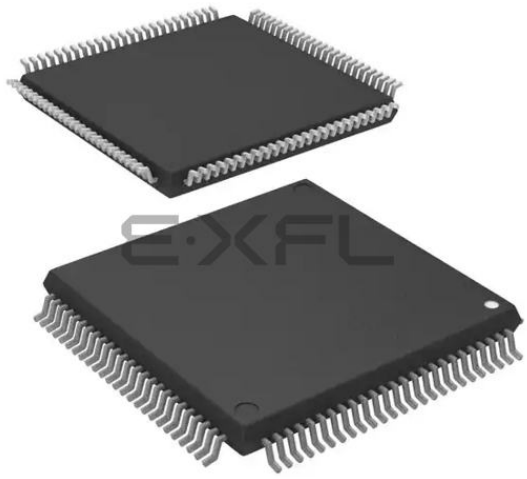
Renesas Electronics America Inc - R5F110PFAFB#30 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART, USB
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	69
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 13x8/12b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f110pfafb-30

○ ROM, RAM capacities

Products with USB

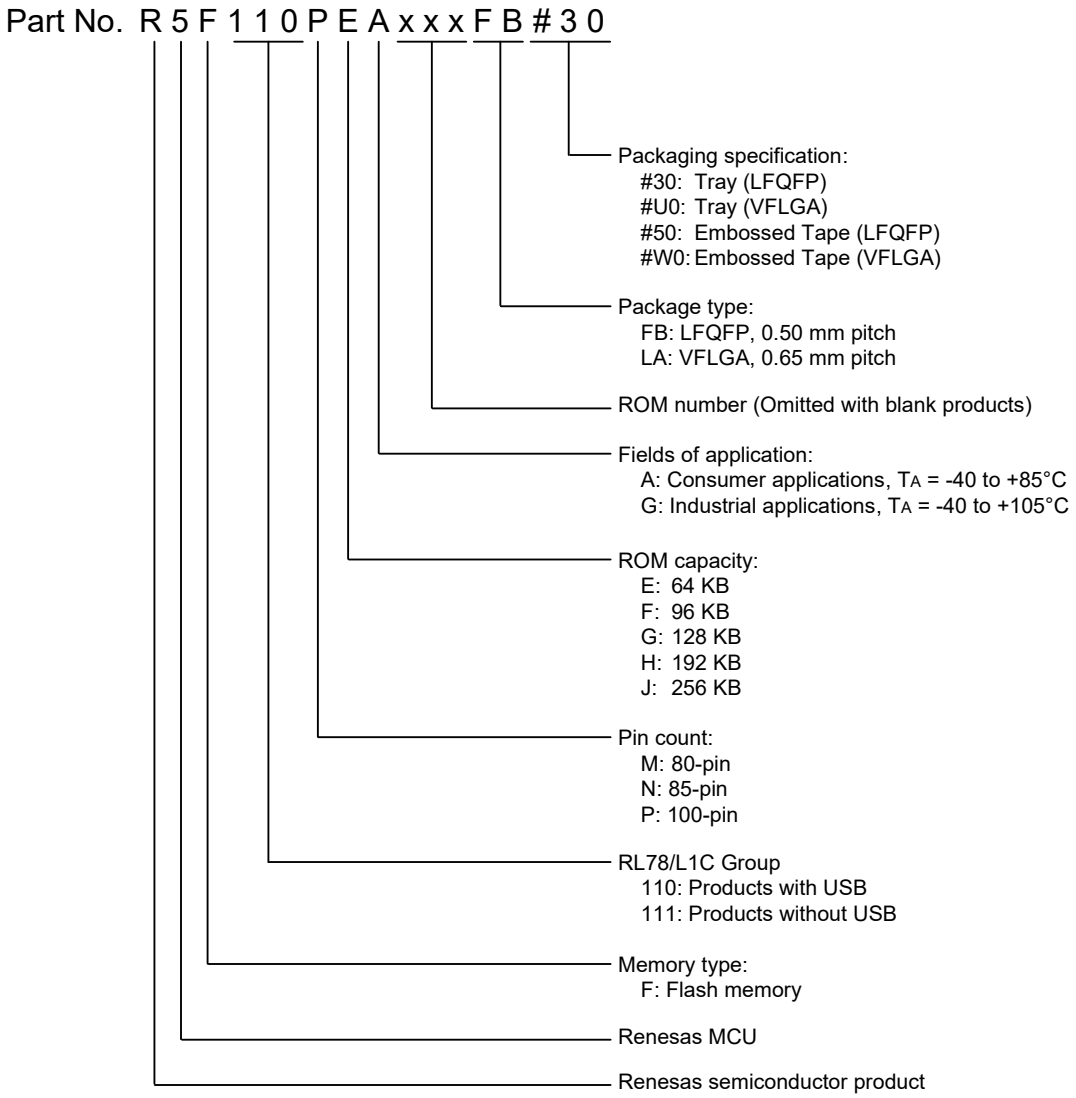
Flash ROM	Data Flash	RAM	RL78/L1C		
			80 pins	85 pins	100 pins
256 KB	8 KB	16 KB Note	R5F110MJ	R5F110NJ	R5F110PJ
192 KB	8 KB	16 KB Note	R5F110MH	R5F110NH	R5F110PH
128 KB	8 KB	12 KB	R5F110MG	R5F110NG	R5F110PG
96 KB	8 KB	10 KB	R5F110MF	R5F110NF	R5F110PF
64 KB	8 KB	8 KB	R5F110ME	R5F110NE	R5F110PE

Products without USB

Flash ROM	Data Flash	RAM	RL78/L1C		
			80 pins	85 pins	100 pins
256 KB	8 KB	16 KB Note	R5F111MJ	R5F111NJ	R5F111PJ
192 KB	8 KB	16 KB Note	R5F111MH	R5F111NH	R5F111PH
128 KB	8 KB	12 KB	R5F111MG	R5F111NG	R5F111PG
96 KB	8 KB	10 KB	R5F111MF	R5F111NF	R5F111PF
64 KB	8 KB	8 KB	R5F111ME	R5F111NE	R5F111PE

Note This is about 15 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/L1C User's Manual).

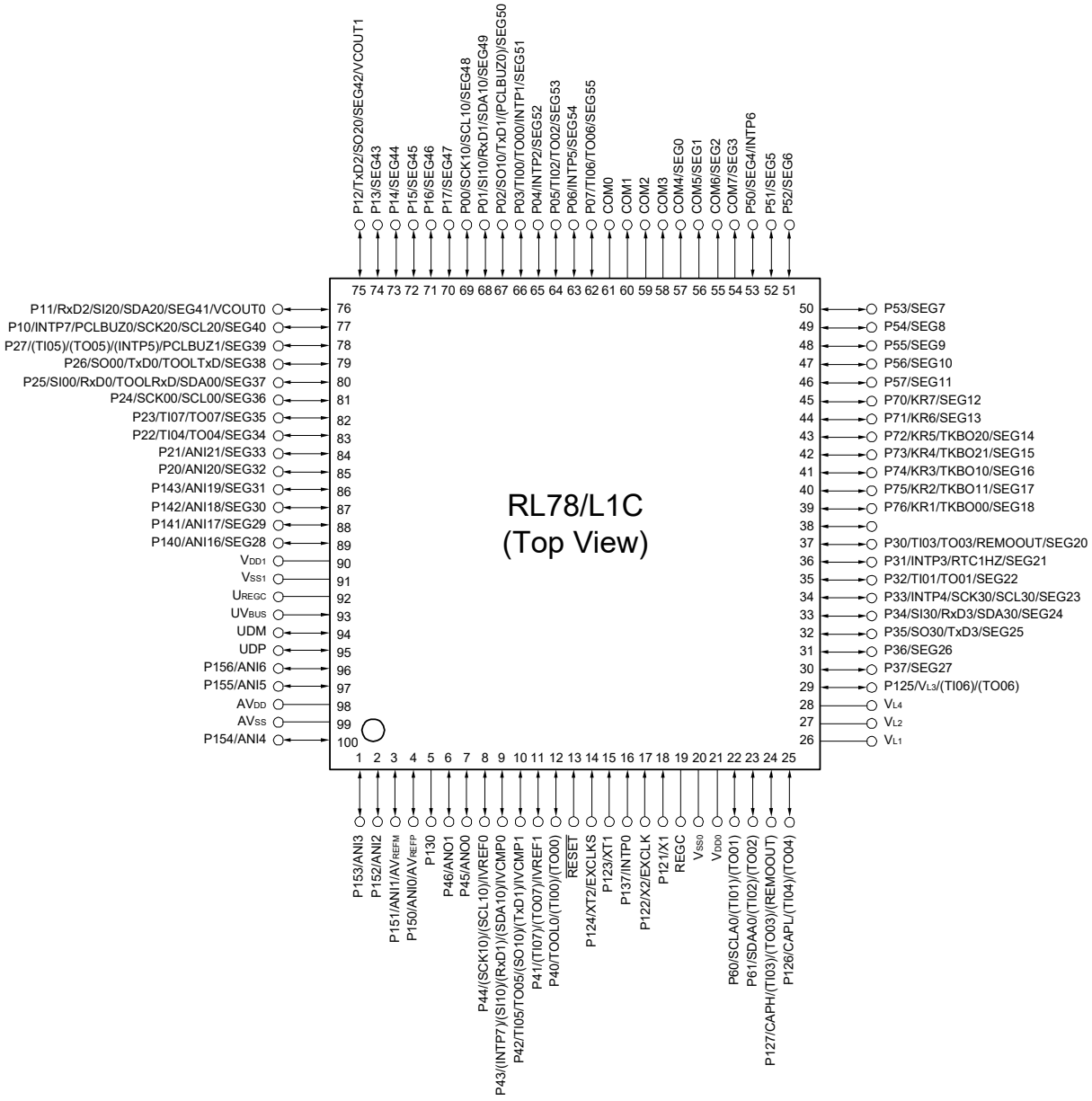
Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1C



Caution Orderable part numbers are current as of when this manual was published.
Please make sure to refer to the relevant product page on the Renesas website for the latest part numbers.

1.3.5 100-pin products (with USB)

• 100-pin plastic LFQFP (fine pitch) (14 × 14 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 µF).

Caution 2. Connect the UREGC pin to Vss pin via a capacitor (0.33 µF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

Absolute Maximum Ratings (T_A = 25°C) (2/3)

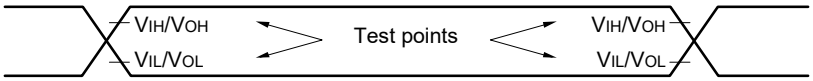
Parameter	Symbols	Conditions		Ratings	Unit
LCD voltage	V_{LI1}	V_{L1} input voltage Note 1		-0.3 to +2.8	V
	V_{LI2}	V_{L2} input voltage Note 1		-0.3 to +6.5	V
	V_{LI3}	V_{L3} input voltage Note 1		-0.3 to +6.5	V
	V_{LI4}	V_{L4} input voltage Note 1		-0.3 to +6.5	V
	V_{LI5}	CAPL, CAPH input voltage Note 1		-0.3 to +6.5	V
	V_{LO1}	V_{L1} output voltage		-0.3 to +2.8	V
	V_{LO2}	V_{L2} output voltage		-0.3 to +6.5	V
	V_{LO3}	V_{L3} output voltage		-0.3 to +6.5	V
	V_{LO4}	V_{L4} output voltage		-0.3 to +6.5	V
	V_{LO5}	CAPL, CAPH output voltage		-0.3 to +6.5	V
	V_{LO6}	COM0 to COM7 SEG0 to SEG55 output voltage	External resistance division method	-0.3 to V_{DD} + 0.3 Note 2	V
			Capacitor split method	-0.3 to V_{DD} + 0.3 Note 2	V
			Internal voltage boosting method	-0.3 to V_{LI4} + 0.3 Note 2	V

Note 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to V_{SS} via a capacitor (0.47 ± 30%) and connect a capacitor (0.47 ± 30%) between the CAPL and CAPH pins.

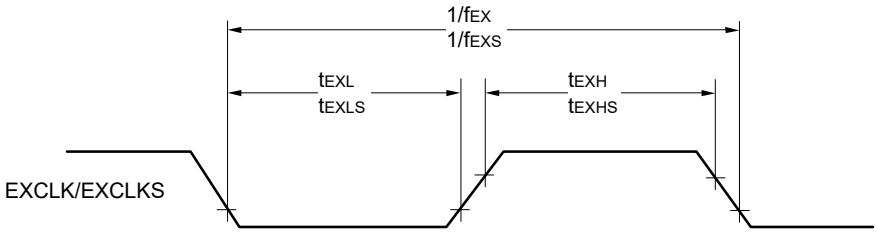
Note 2. Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

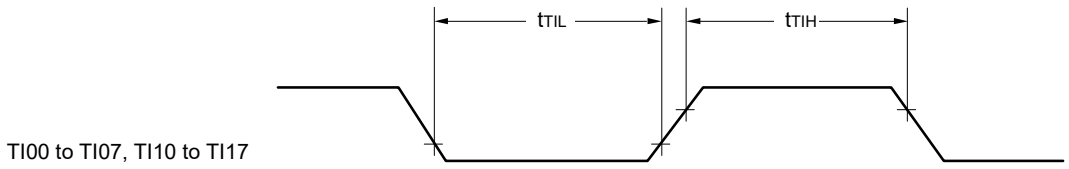
AC Timing Test Points

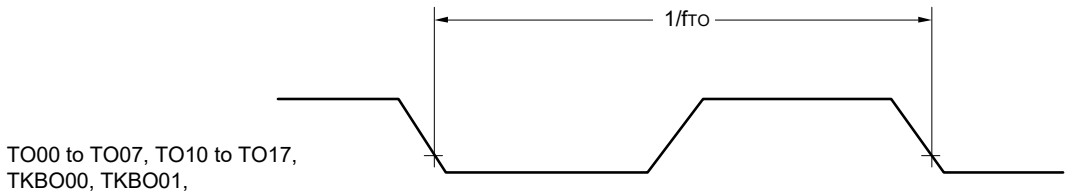


External System Clock Timing

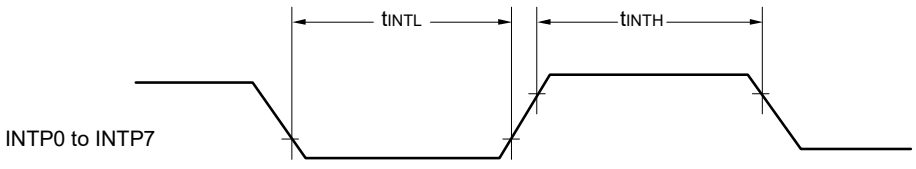


TI/TO Timing

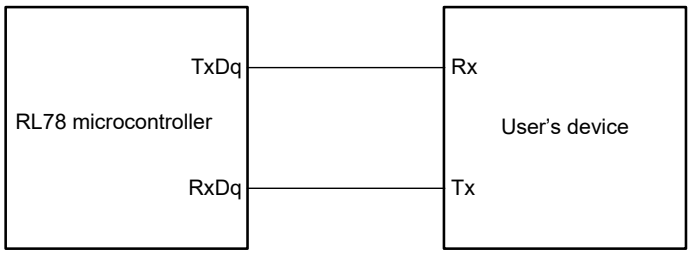




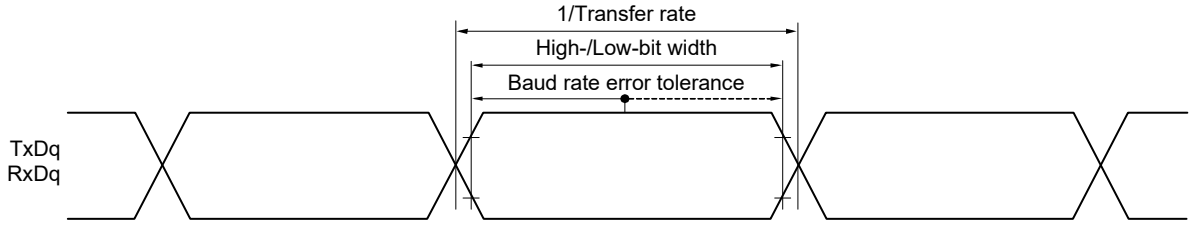
Interrupt Request Input Timing



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85°C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} < 3.6 V	f_{MCK} > 16 MHz	8/f_{MCK}		—		—		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.6 V		6/f_{MCK} and 500		6/f_{MCK} and 500		6/f_{MCK} and 500		ns
		1.8 V ≤ V_{DD} < 3.6 V		—		6/f_{MCK} and 750		6/f_{MCK} and 750		ns
		1.6 V ≤ V_{DD} < 3.6 V		—		—		6/f_{MCK} and 1500		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		ns
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		t_{KCY1}/2 - 66		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} < 3.6 V		—		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.6 V ≤ V_{DD} < 3.6 V		—		—		1/f_{MCK} + 40		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	2.4 V ≤ V_{DD} < 3.6 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ V_{DD} < 3.6 V		—		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.6 V ≤ V_{DD} < 3.6 V		—		—		1/f_{MCK} + 250		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 44		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			2.4 V ≤ V_{DD} < 3.6 V		2/f_{MCK} + 75		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			1.8 V ≤ V_{DD} < 3.6 V		—		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			1.6 V ≤ V_{DD} < 3.6 V		—		—		2/f_{MCK} + 220	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

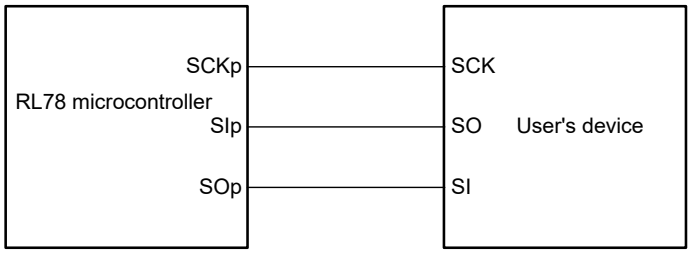
Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)

Remark 2. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

CSI mode connection diagram (during communication at same potential)



Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(8) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	177		479		479		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		195		195		195	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		483		483		483	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

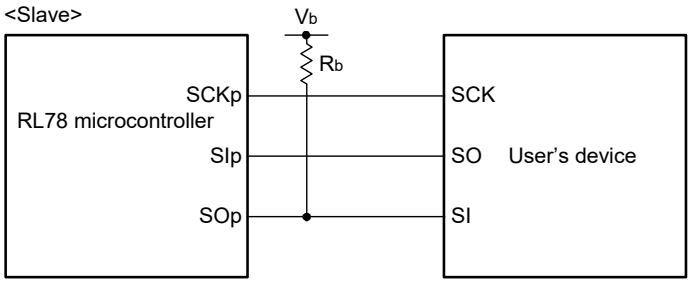
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with V_{DD} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

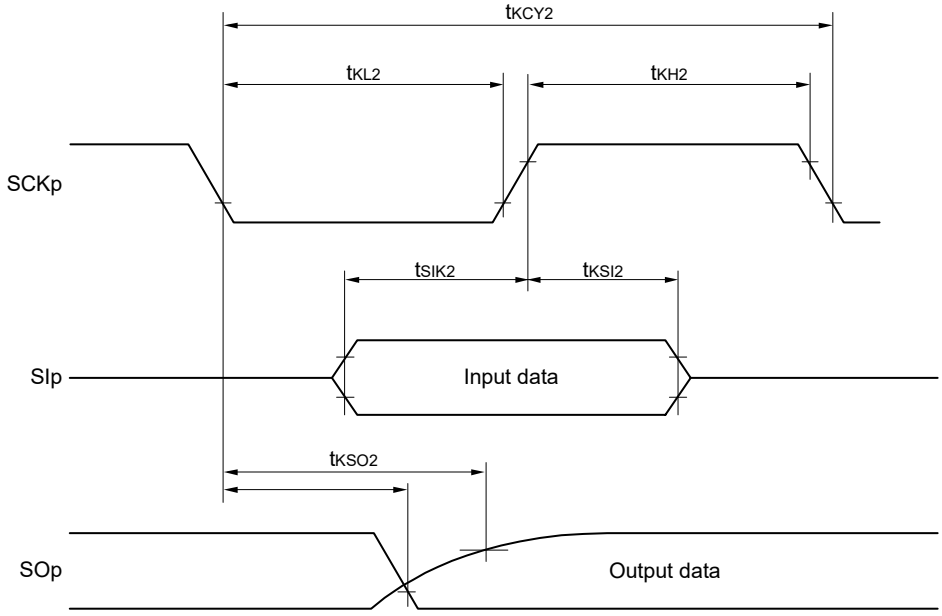


Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

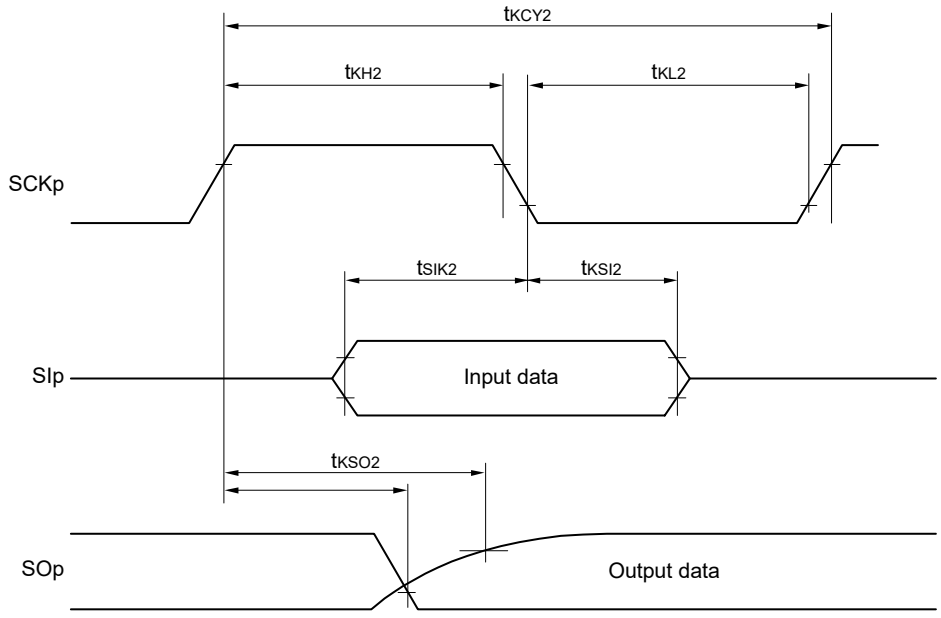
Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

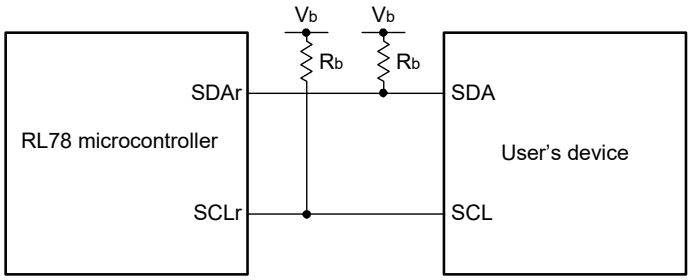


CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

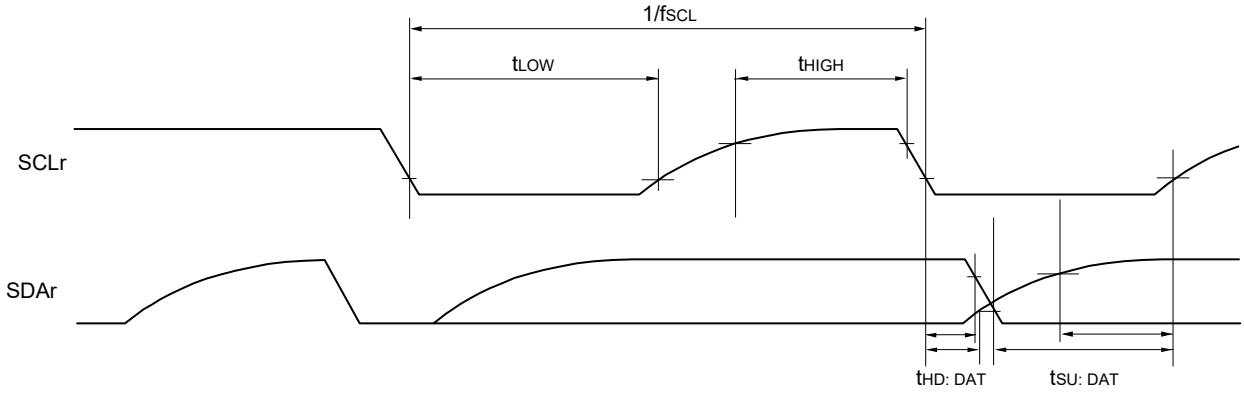


Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM, POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 02, 10, 12)

2.5.3 USB

(1) Electrical specifications

(T_A = -40 to +85°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
U_{REGC}	U_{REGC} output voltage characteristic	U_{REGC}	UV_{BUS} = 4.0 to 5.5 V, PXXCON = VDDUSBE = 1	3.0	3.3	3.6	V
UV_{BUS}	UV_{BUS} input voltage characteristic	UV_{BUS}	Function	4.35 (4.02 Note)	5.00	5.25	V

Note Value of instantaneous voltage

(T_A = -40 to +85°C, 4.35 V ≤ UV_{BUS} ≤ 5.25 V, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input characteristic (FS/LS receiver)	Input voltage		V_{IH}		2.0			V
			V_{IL}				0.8	V
	Difference input sensitivity		V_{DI}	| UDP voltage - UDM voltage |	0.2			V
	Difference common mode range		V_{CM}		0.8		2.5	V
Output characteristic (FS driver)	Output voltage		V_{OH}	I_{OH} = -200 µA	2.8		3.6	V
			V_{OL}	I_{OL} = 2 mA	0		0.3	V
	Transition time	Rising	t_{FR}	Rising: From 10% to 90% of amplitude, Falling: From 90% to 10% of amplitude, CL = 50 pF	4		20	ns
		Falling	t_{FF}		4		20	ns
	Matching (TFR/TFF)		V_{FRFM}		90		111.1	%
	Crossover voltage		V_{FCRS}		1.3		2.0	V
	Output Impedance		Z_{DRV}		28		44	Ω
Output characteristic (LS driver)	Output voltage		V_{OH}		2.8		3.6	V
			V_{OL}		0		0.3	V
	Transition time	Rising	t_{LR}	Rising: From 10% to 90% of amplitude, Falling: From 90% to 10% of amplitude, CL = 250 pF to 750 pF The UDP and UDM pins are individually pulled down via 15 kΩ	75		300	ns
		Falling	t_{LF}		75		300	ns
	Matching (TFR/TFF) Note		V_{LTFM}		80		125	%
	Crossover voltage Note		V_{LCRS}		1.3		2.0	V
Pull-up, Pull-down	Pull-down resistor		R_{PD}		14.25		24.80	kΩ
	Pull-up resistor	Idle	R_{PUI}		0.9		1.575	kΩ
		Reception	R_{PUA}		1.425		3.09	kΩ
UV_{BUS}	UV_{BUS} pull-down resistor		R_{VBUS}	UV_{BUS} voltage = 5.5 V		1000		kΩ
	UV_{BUS} input voltage		V_{IH}		3.20			V
			V_{IL}				0.8	V

Note Excludes the first signal transition from the idle state.

(5) Communication at different potential (1.8 V, 2.5 V) (UART mode)

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate Notes 1, 2		Reception	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/12 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 4		2.0	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/12 Notes 1, 2, 3	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 4		1.3	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with V_{DD} ≥ V_b.

Note 3. The following conditions are required for low voltage interface.
2.4 V ≤ V_{DD} < 2.7 V: MAX. 2.6 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	354		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	958		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		390	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		966	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	88		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	220		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		50	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

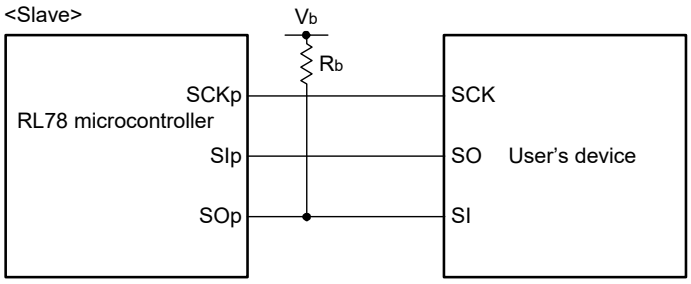
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with V_{DD} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

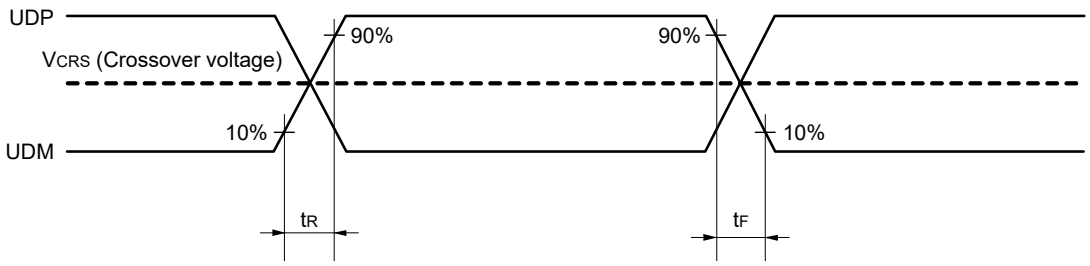


Remark 1. Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +105°C, 4.35 V ≤ UVBUS ≤ 5.25 V, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB standard BC1.2	UDP sink current	IDP_SINK		25	100	175	μA
	UDM sink current	IDM_SINK		25	100	175	μA
	DCD source current	IDP_SRC		7	10	13	μA
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 μA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 μA	0.5	0.6	0.7	V

(4) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.5	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	4.125			µs
Zero-scale error Note 1	EZS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.5	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.5	LSB
Analog input voltage	VAIN			0		AV_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 2			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to **3.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(5) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6, ANI16 to ANI21

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 2.4 V ≤ V_{DD}, 2.4 V ≤ AV_{DD} = V_{DD}, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AV_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tCONV	8-bit resolution	16.0			µs
Zero-scale error Note	EZS	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Reference voltage (+)	$AV_{REF(+)}$	= Internal reference voltage (V_{BGR})	1.38	1.45	1.5	V
Analog input voltage	VAIN		0		V_{BGR}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

3.6.2 Temperature sensor, internal reference voltage output characteristics

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V (HS (high-speed main) mode))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tAMP		10			µs

3.6.3 D/A converter characteristics

(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	2.4 V ≤ V_{DD} ≤ 3.6 V			±2.5	LSB
		Rload = 8 MΩ	2.4 V ≤ V_{DD} ≤ 3.6 V			±2.5	LSB
Settling time	tSET	Cload = 20 pF	2.7 V ≤ V_{DD} ≤ 3.6 V			3	µs
			2.4 V ≤ V_{DD} < 2.7 V			6	µs

REVISION HISTORY	RL78/L1C Datasheet

Rev.	Date	Description	
		Page	Summary
2.00	Feb 21, 2014	4	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1C
		69	Modification of (1) Electrical specifications in 2.5.3 USB
		82	Modification of note 1 in (1) 1/3 bias method in 2.8.2 Internal voltage boosting method
		130	Modification of (1) Electrical specifications in 3.5.3 USB
		142	Modification of note 1 in (1) 1/3 bias method in 3.8.2 Internal voltage boosting method
2.10	Aug 12, 2016	5	Addition of product name (RL78/L1C) and description (Top View) in 1.3.1 80-pin products (with USB)
		6	Addition of product name (RL78/L1C) and description (Top View) in 1.3.2 80-pin products (without USB)
		9	Addition of product name (RL78/L1C) and description (Top View) in 1.3.5 100-pin products (with USB)
		10	Addition of product name (RL78/L1C) and description (Top View) in 1.3.6 100-pin products (without USB)
		17, 19	Modification of 1.6 Outline of Functions
		23	Modification of description in Absolute Maximum Ratings (T_A = 25°C)
		26, 27	Modification of description in 2.3.1 Pin characteristics
		39, 40	Modification of the graph for Minimum Instruction Execution Time during Main System Clock Operation
		72	Modification of conditions in (1) of 2.6.1 A/D converter characteristics
		85	Modification of the title and note in 2.9 RAM Data Retention Characteristics
		85	Modification of conditions in 2.10 Flash Memory Programming Characteristics
		87	Modification of description in 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = -40 to +105 °C)
		88, 90	Modification of description in Absolute Maximum Ratings (T_A = 25°C)
		93, 94, 96	Modification of description in 3.3.1 Pin characteristics
		106	Modification of the graph for Minimum Instruction Execution Time during Main System Clock Operation
		144	Modification of the title and note in 3.9 RAM Data Retention Characteristics
		145	Modification of conditions and addition of note 4 in 3.10 Flash Memory Programming Characteristics
2.20	Dec 28, 2017	13	Modification of figure in 1.5.2 80/85-pin products (without USB)
		17, 19	Modification of tables in 1.6 Outline of Functions
		26, 27	Modification of table and note 3 in 2.3.1 Pin characteristics
		85	Modification of figure in 2.12 Timing of Entry to Flash Memory Programming Modes
		89	Modification of table in 3.1 Absolute Maximum Ratings
		92, 93	Modification of table and note 3 in 3.3.1 Pin characteristics
		144	Modification of figure in 3.12 Timing of Entry to Flash Memory Programming Modes